TOSHIBA Transistor Silicon NPN Epitaxial Planar Type (PCT process)

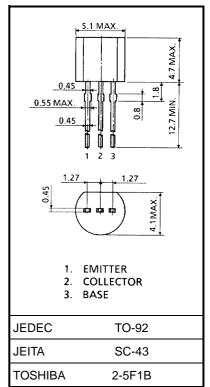
2SC1923

High Frequency Amplifier Applications FM, RF, MIX, IF Amplifier Applications

- Small reverse transfer capacitance: C_{re} = 0.7 pF (typ.)
- Low noise figure: NF = 2.5dB (typ.) (f = 100 MHz)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	40	V
Collector-emitter voltage	V _{CEO}	30	V
Emitter-base voltage	V _{EBO}	4	V
Collector current	Ι _C	20	mA
Base current	Ι _Β	4	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C



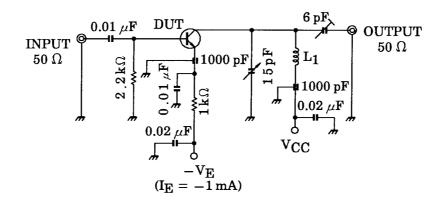
Weight: 0.21 g (typ.)

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 18 V, I_{E} = 0$		_	0.5	μA
Emitter cut-off current	I _{EBO}	$V_{EB} = 4 V$, $I_C = 0$	_	_	0.5	μA
DC current gain	h _{FE} (Note)	$V_{CE} = 6 \text{ V}, \text{ I}_{C} = 1 \text{ mA}$	40		200	
Reverse transfer capacitance	C _{re}	V _{CE} = 6 V, f = 1 MHz	_	0.70	_	pF
Transition frequency	f _T	$V_{CE} = 6 V, I_{C} = 1 mA$	_	550	_	MHz
Collector-base time constant	C _c .r _{bb'}	$V_{CE} = 6 \text{ V}, \text{ I}_{E} = -1 \text{ mA}, \text{ f} = 30 \text{ MHz}$	_	_	30	ps
Noise figure	NF	V _{CE} = 6 V, I _E = -1 mA, f = 100 MHz, Figure 1		2.5	4.0*	dB
Power gain	G _{pe}		15	18	_	dB

Note: hFE classification R: 40~80, O: 70~140, Y: 100~200 (* NF = 5.0dB max)

Unit: mm



L1: 0.8 mm | silver plated copper wire, 4 T, 10ID, 8 LENGTH



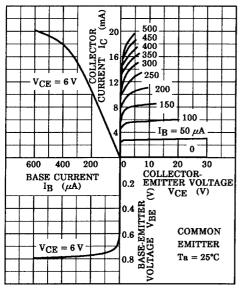
y Parameter (typ.)

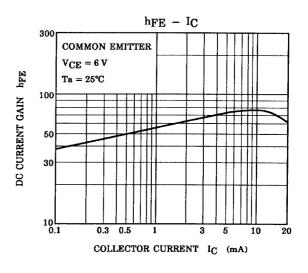
(1) Common emitter (V _{CE} = 6 V, I _E = -1 mA, f = 100 MHz)				
Characteristics	Symbol	Тур.	Unit	
Input conductance	gie	2.9	mS	
Input capacitance	C _{ie}	10.2	pF	
Reverse transfer admittance	y _{re}	0.33	μS	
Phase angle of reverse transfer admittance	θ_{re}	-90	o	
Forward transfer admittance	y _{fe}	40	mS	
Phase angle of forward transfer admittance	θ_{fe}	-20	o	
Output conductance	goe	45	μS	
Output capacitance	C _{oe}	1.1	pF	

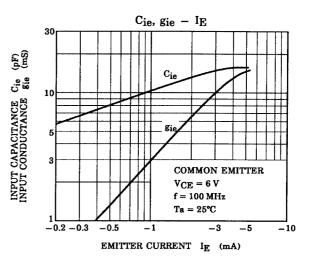
(2) Common base ($V_{CE} = 6 V$, $I_E = -1 mA$, f = 100 MHz)

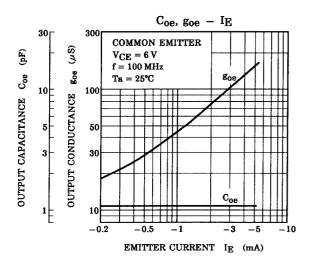
Characteristics	Symbol	Тур.	Unit
Input conductance	gib	34	mS
Input capacitance	C _{ib}	-10	pF
Reverse transfer admittance	y _{rb}	0.27	μS
Phase angle of reverse transfer admittance	θ _{rb}	-105	o
Forward transfer admittance	y _{fb}	34	mS
Phase angle of forward transfer admittance	θ_{fb}	165	o
Output conductance	9 _{ob}	45	μS
Output capacitance	C _{ob}	1.1	pF

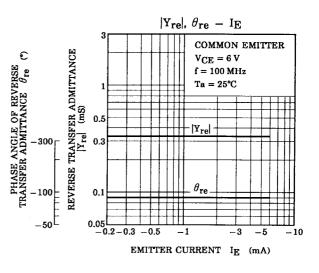
STATIC CHARACTERISTICS



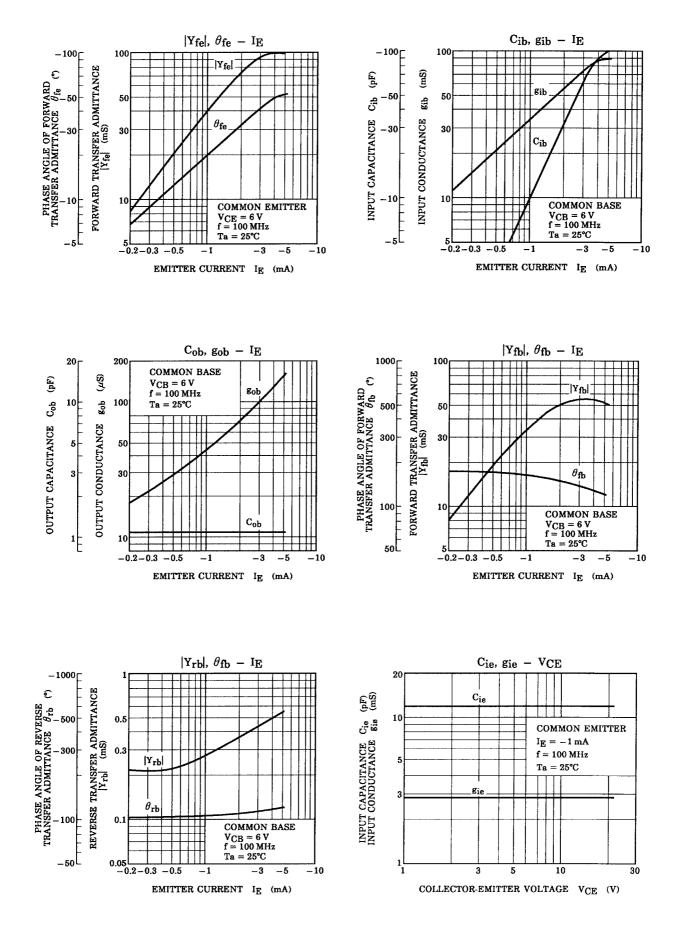




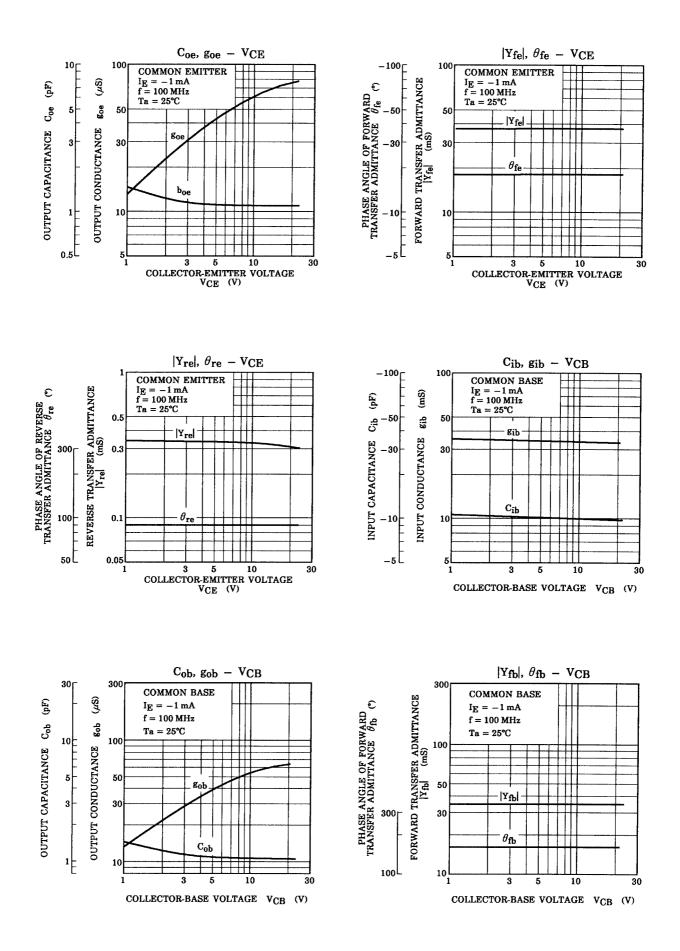




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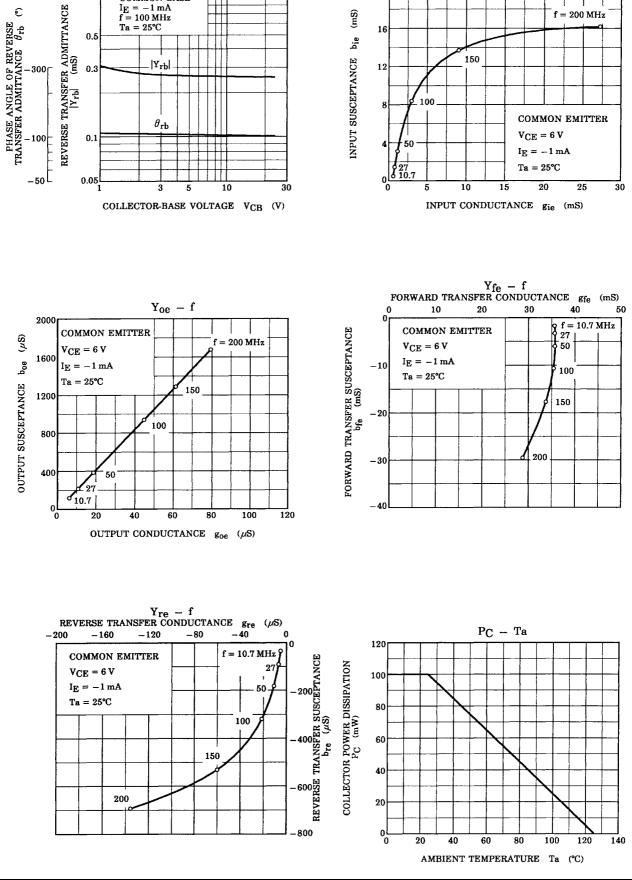
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 $|Y_{rb}|, \theta_{rb} - VCB$

COMMON BASE

 $Y_{ie} - f$

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